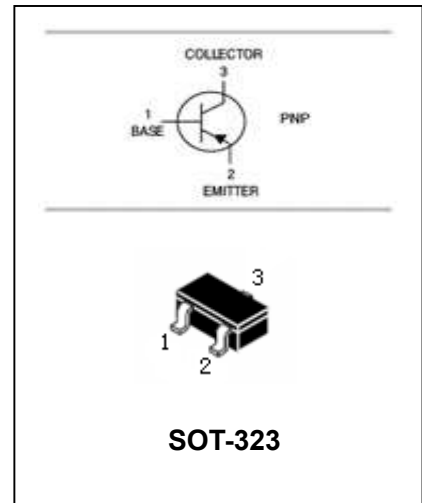


PNP Silicon Epitaxial Planar Transistor

2SA1579

FEATURES

- Power dissipation.($P_C=200\text{mW}$)
- Excellent H_{FE} Linearity.



APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1579	RP/ RR/RS	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

PNP Silicon Epitaxial Planar Transistor

2SA1579

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -100V, I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -2mA$	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.5	V
Transition frequency	f_T	$V_{CE} = -12V, I_C = -2mA$ $f = 30MHz$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -12V, I_E = 0, f = 1MHz$		3.2		pF

CLASSIFICATION OF h_{FE}

Rank	P	R	S
Range	120-270	180-390	270-560
marking	RP	RR	RS

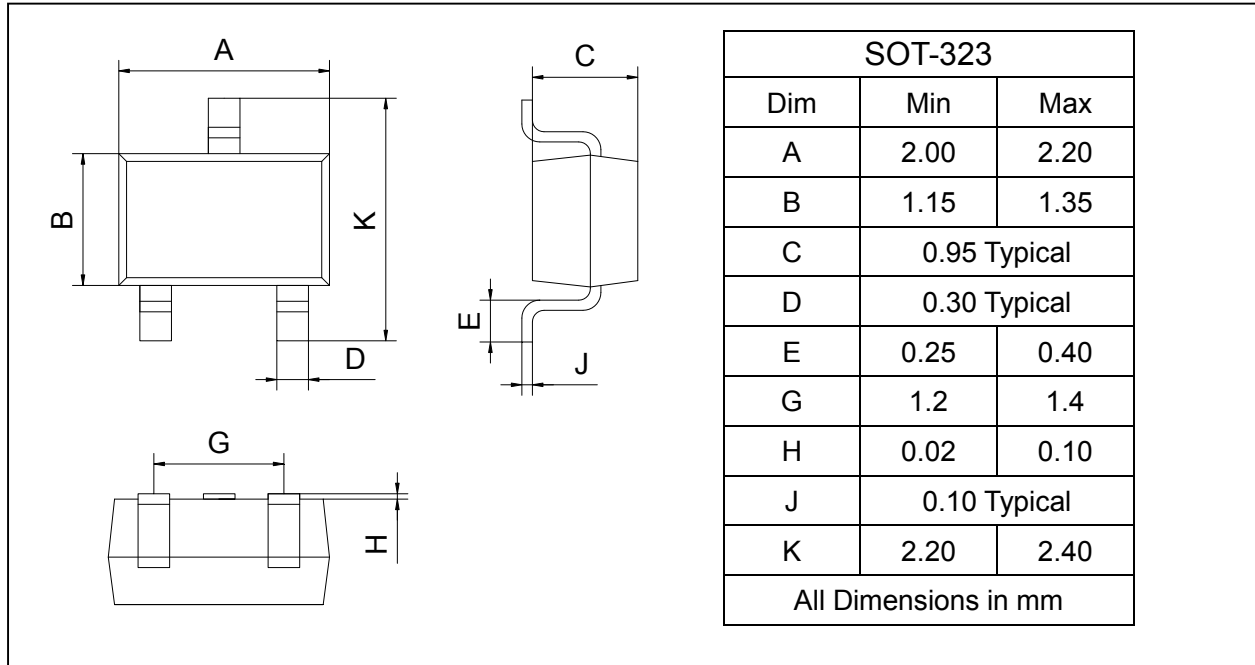
PNP Silicon Epitaxial Planar Transistor

2SA1579

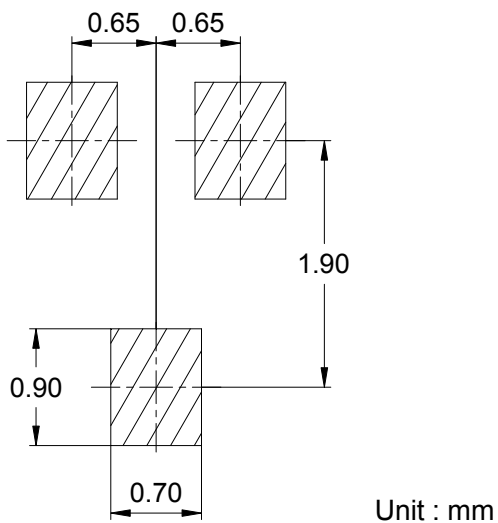
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1579	SOT-323	3000/Tape&Reel